

TYPES 2N1722A, 2N1724A

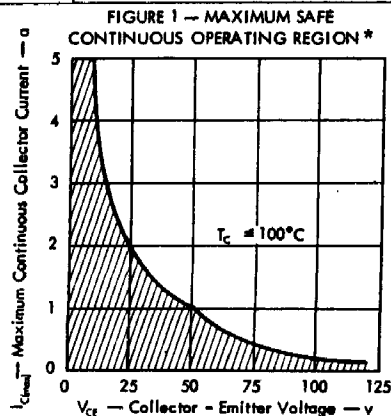
N-P-N TRIPLE-DIFFUSED MESA SILICON TRANSISTORS

*electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
BV_{CEO} Collector-Emitter Breakdown Voltage	$I_C = 200 \text{ ma}, I_B = 0$, (See Notes 4 and 7)	120		v
I_{CBO} Collector Cutoff Current	$V_{CB} = 3 \text{ v}, I_E = 0$		0.1	ma
I_{CES} Collector Cutoff Current	$V_{CE} = 60 \text{ v}, V_{BE} = 0$, (See Note 5)		0.1	ma
	$V_{CE} = 100 \text{ v}, V_{BE} = 0$, (See Note 5)		1.0	
	$V_{CE} = 100 \text{ v}, V_{BE} = 0, T_C = 150^\circ\text{C}$, (See Note 5)		2.0	
	$V_{CE} = 180 \text{ v}, V_{BE} = 0, T_C = 150^\circ\text{C}$, (See Note 5)		10	
I_{EBO} Emitter Cutoff Current	$V_{EB} = 9 \text{ v}, I_C = 0$		0.5	ma
	$V_{EB} = 10 \text{ v}, I_C = 0$		10	
V_{EB1} Emitter-Base Floating Potential	$V_{CB} = 180 \text{ v}, I_B = 0$		1.0	v
h_{FE} Static Forward Current Transfer Ratio	$V_{CE} = 15 \text{ v}, I_C = 100 \text{ ma}$, (See Note 4)	30		
	$V_{CE} = 15 \text{ v}, I_C = 2 \text{ a}$, (See Note 4)	30	90	
	$V_{CE} = 15 \text{ v}, I_C = 2 \text{ a}, T_C = -55^\circ\text{C}$, (See Note 4)	18		
	$V_{CE} = 5 \text{ v}, I_C = 5 \text{ a}$, (See Note 4)	20		
V_{BE} Base-Emitter Voltage	$I_B = 200 \text{ ma}, I_C = 2 \text{ a}$, (See Note 4)		1.2	v
	$I_B = 500 \text{ ma}, I_C = 5 \text{ a}$, (See Note 4)		2.0	
$V_{CE(sat)}$ Collector-Emitter Saturation Voltage	$I_B = 200 \text{ ma}, I_C = 2 \text{ a}, T_C = -55^\circ\text{C}$, (See Note 4)		0.6	v
	$I_B = 500 \text{ ma}, I_C = 5 \text{ a}$, (See Note 4)		1.5	
$ h_{fe} $ Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = 15 \text{ v}, I_C = 500 \text{ ma}, f = 10 \text{ mc}$, (See Note 6)	1.0		
C_{ob} Common-Base Open-Circuit Output Capacitance	$V_{CB} = 15 \text{ v}, I_E = 0, f = 1.0 \text{ mc}$		550	pf

*thermal characteristics

PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
θ_{J-C} Junction-to-Case Thermal Resistance			1.5	$^\circ\text{C}/\text{w}$
θ_{J-A} Junction-to-Free-Air Thermal Resistance			50	$^\circ\text{C}/\text{w}$



NOTES: 4. These parameters must be measured using pulse techniques. PW = 300 μsec , Duty Cycle $\leq 2\%$.

5. For correct measurement of I_{CES} , the base must be shorted to the emitter. The current meter must not be placed in the base-emitter, short-circuit loop. I_{CES} may be used in place of I_{CBO} for circuit-stability calculations.

6. If tested without a heat sink, DC collector current must not be applied longer than 5 seconds.

7. Other pulse widths or duty cycles may be used for the measurement of collector-emitter breakdown voltage with results similar to those obtained using the conditions specified in Note 4, providing that collector current is limited to 200 ma and case temperature is limited to less than 40°C over a 5 second (or less) measurement period.

*Indicates JEDEC registered data